

TOSHIBA Power Transistor Module Silicon NPN Epitaxial Type
(Four Darlingtons Power Transistors 4 in One)

MP4013

High Power Switching Applications

Hammer Drive, Pulse Motor Drive and Inductive Load Switching

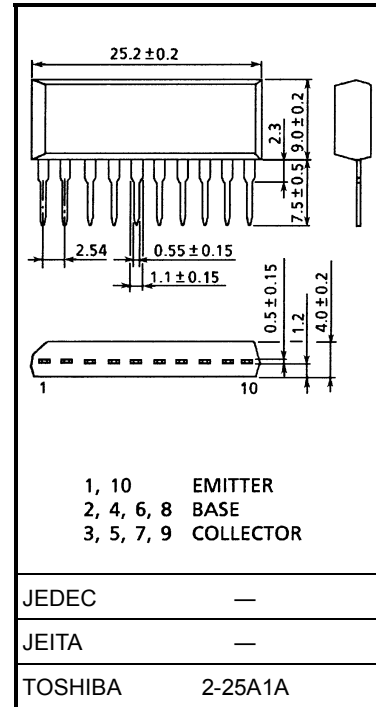
- Small package by full molding (SIP 10 pins)
- High collector power dissipation (4-device operation)
: $P_T = 4\text{ W}$ ($T_a = 25^\circ\text{C}$)
- High collector current: I_C (DC) = 2 A (max)
- High DC current gain: $h_{FE} = 2000$ (min) ($V_{CE} = 2\text{ V}$, $I_C = 1\text{ A}$)
- Zener diode included between collector and base.

Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics		Symbol	Rating	Unit
Collector-base voltage		V_{CBO}	80 ± 10	V
Collector-emitter voltage		V_{CEO}	80 ± 10	V
Emitter-base voltage		V_{EBO}	8	V
Collector current	DC	I_C	2	A
	Pulse	I_{CP}	3	
Continuous base current		I_B	0.5	A
Collector power dissipation (1-device operation)		P_C	2.0	W
Collector power dissipation (4-device operation)		P_T	4.0	W
Junction temperature		T_j	150	$^\circ\text{C}$
Storage temperature range		T_{stg}	-55 to 150	$^\circ\text{C}$

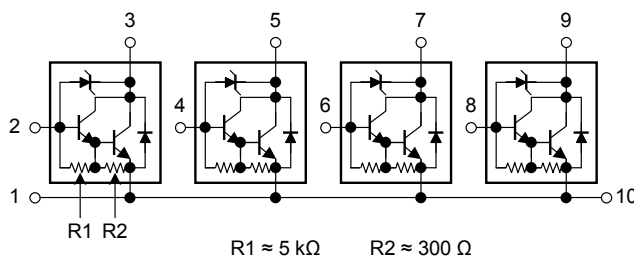
Industrial Applications

Unit: mm



Weight: 2.1 g (typ.)

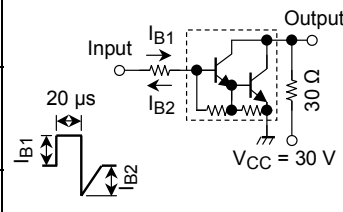
Array Configuration



Thermal Characteristics

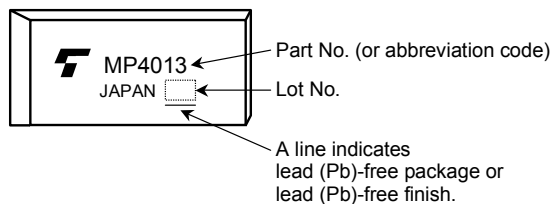
Characteristics	Symbol	Max	Unit
Thermal resistance from junction to ambient (4 devices operation, $T_a = 25^\circ\text{C}$)	$\Sigma R_{th(j-a)}$	31.3	$^\circ\text{C/W}$
Maximum lead temperature for soldering purposes (3.2 mm from case for 10 s)	T_L	260	$^\circ\text{C}$

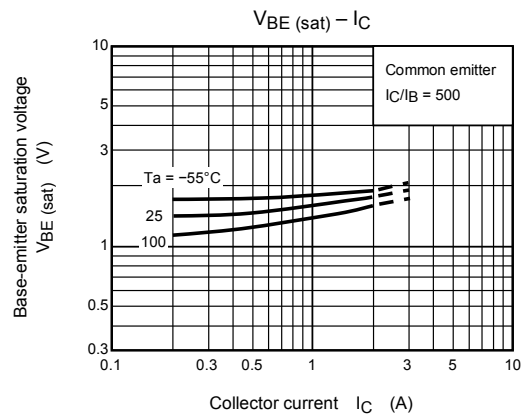
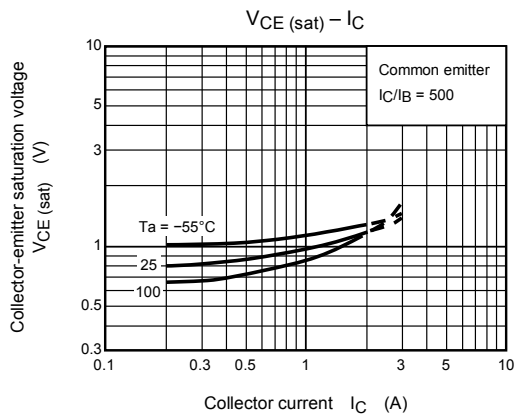
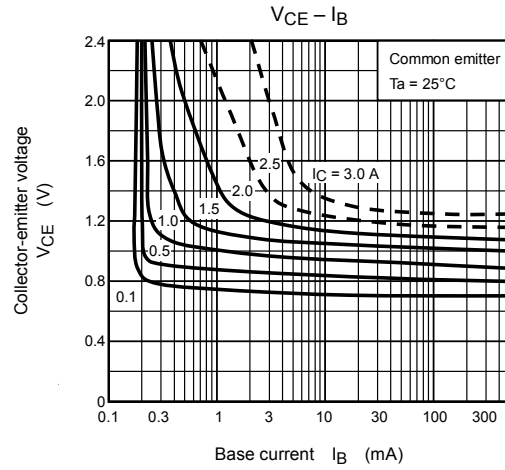
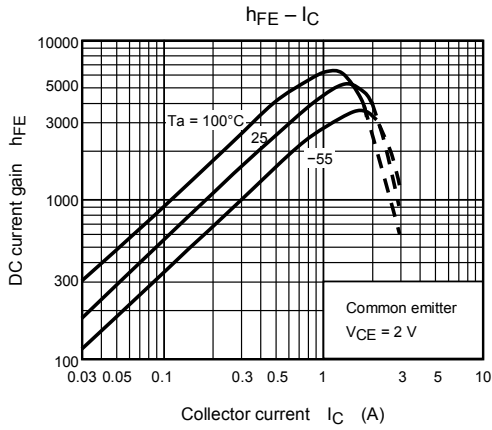
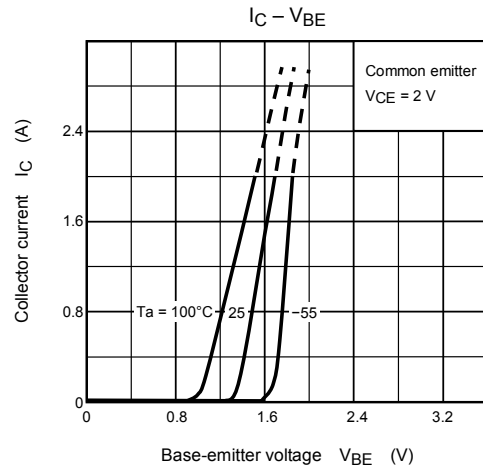
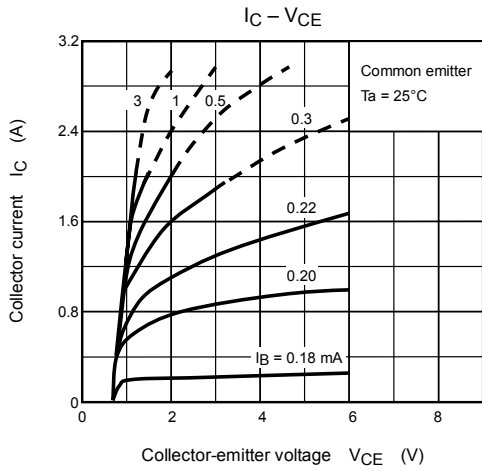
Electrical Characteristics ($T_a = 25^\circ\text{C}$)

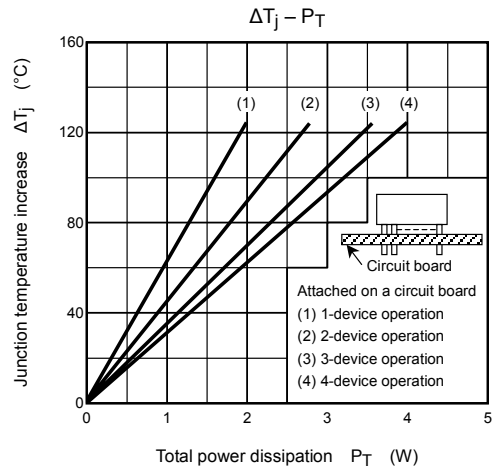
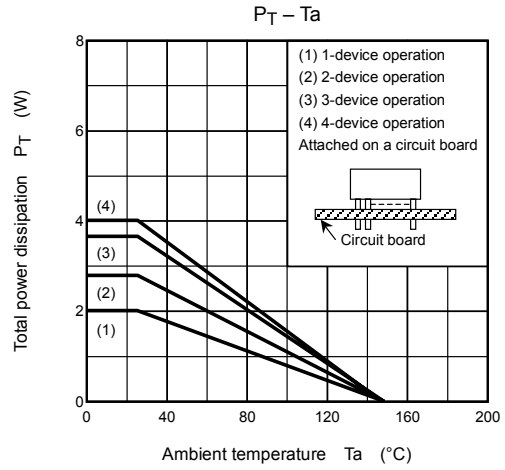
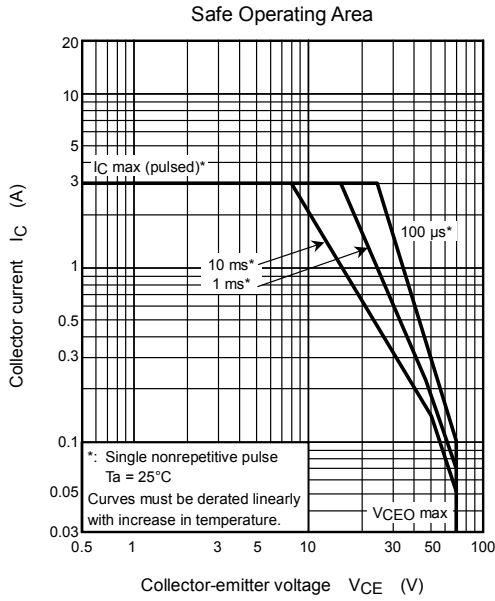
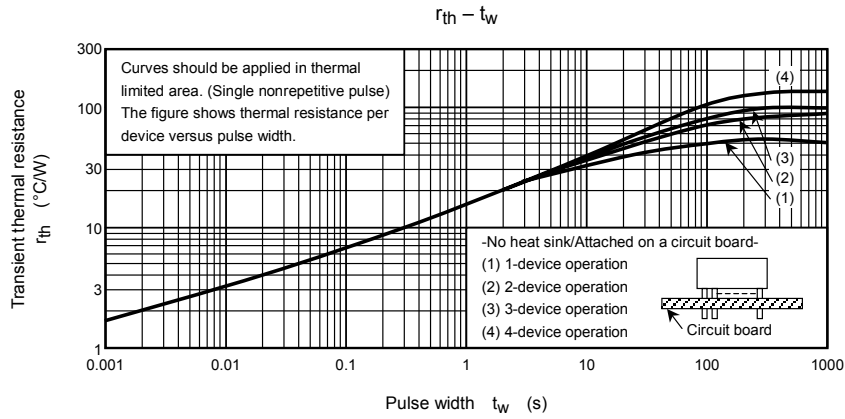
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current		I_{CBO}	$V_{CB} = 60\text{ V}, I_E = 0\text{ A}$	—	—	10	μA
Collector cut-off current		I_{CEO}	$V_{CE} = 60\text{ V}, I_B = 0\text{ A}$	—	—	10	μA
Emitter cut-off current		I_{EBO}	$V_{EB} = 8\text{ V}, I_C = 0\text{ A}$	0.8	—	4.0	mA
Collector-base breakdown voltage		$V_{(BR)CBO}$	$I_C = 100\ \mu\text{A}, I_E = 0\text{ A}$	70	80	90	V
Collector-emitter breakdown voltage		$V_{(BR)CEO}$	$I_C = 10\text{ mA}, I_B = 0\text{ A}$	70	80	90	V
DC current gain		$h_{FE(1)}$	$V_{CE} = 2\text{ V}, I_C = 1\text{ A}$	2000	—	—	—
Saturation voltage	Collector-emitter	$V_{CE(sat)}$	$I_C = 1\text{ A}, I_B = 1\text{ mA}$	—	—	1.5	V
	Base-emitter	$V_{BE(sat)}$	$I_C = 1\text{ A}, I_B = 1\text{ mA}$	—	—	2.0	
Transition frequency		f_T	$V_{CE} = 2\text{ V}, I_C = 0.5\text{ A}$	—	100	—	MHz
Collector output capacitance		C_{ob}	$V_{CB} = 10\text{ V}, I_E = 0\text{ A}, f = 1\text{ MHz}$	—	20	—	pF
Switching time	Turn-on time	t_{on}		—	0.4	—	μs
	Storage time	t_{stg}		—	4.0	—	
	Fall time	t_f		—	0.6	—	

$I_{B1} = -I_{B2} = 1\text{ mA}, \text{duty cycle} \leq 1\%$

Marking







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